

BR2500M - BR2510M

PRV : 50 - 1000 Volts

I_o : 25 Amperes

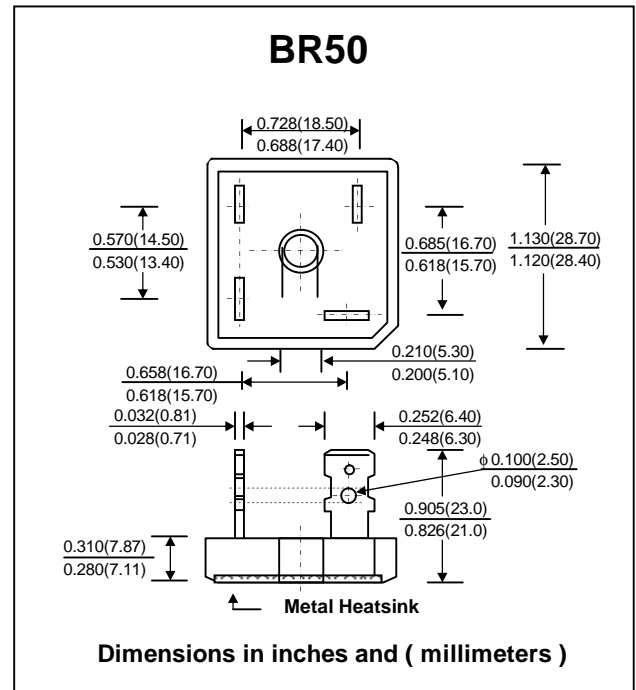
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : Metal Case
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : plated .25" (6.35 mm). Faston
- * Polarity : Polarity symbols marked on case
- * Mounting position : Bolt down on heat-sink with silicone thermal compound between bridge and mounting surface for maximum heat transfer efficiency.
- * Weight : 17.1 grams

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

RATING	SYMBOL	BR2500 M	BR2501 M	BR2502 M	BR2504 M	BR2506 M	BR2508 M	BR2510 M	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current T _c = 55°C	I _{F(AV)}	25							A
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I _{FSM}	300							A
Current Squared Time at t < 8.3 ms.	I ² t	375							A ² S
Maximum Forward Voltage per Diode at I _F = 12.5 A	V _F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	T _a = 25 °C	10							μA
	T _a = 100 °C	200							μA
Typical Thermal Resistance (Note 1)	R _{θJC}	1.45							°C/W
Operating Junction Temperature Range	T _J	- 40 to + 150							°C
Storage Temperature Range	T _{STG}	- 40 to + 150							°C

Notes :

1. Thermal Resistance from junction to case with units mounted on a 5" x 6" x 4.9" (12.8cm.x 15.2cm.x 12.4cm.) Al.-Finned Plate

RATING AND CHARACTERISTIC CURVES (BR2500 - BR2510M)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

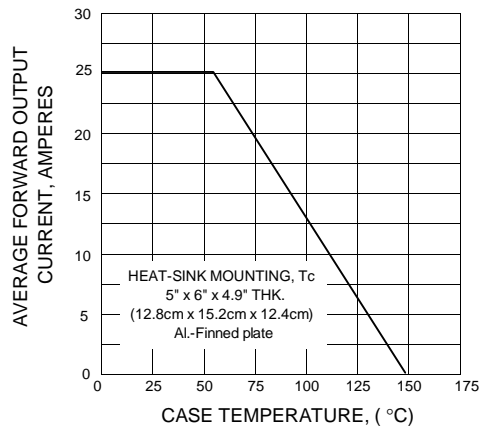


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

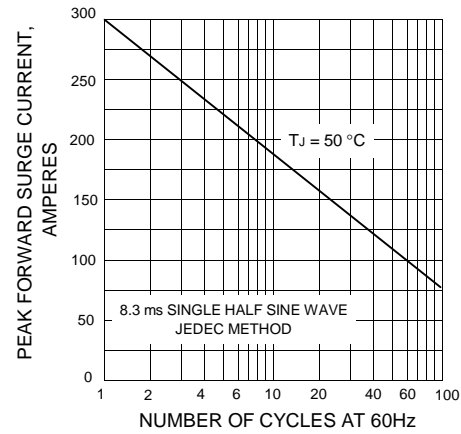


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

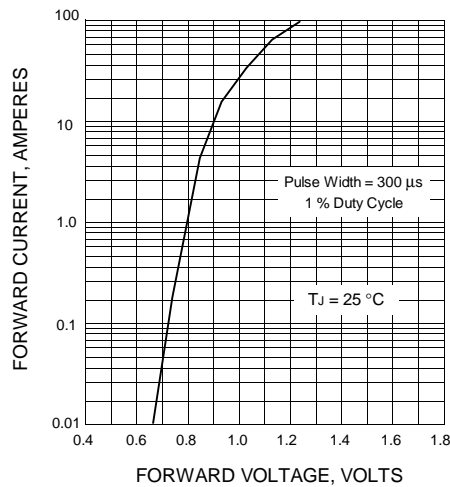


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

